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Abstract

Semiconductor arrangement having nonvolatile memories

The invention relates to a semiconductor arrangement having at least one nonvolatile memory cell which has a first electrode comprising at least two layers; and having an organic material, the organic material forming a compound with that layer of the first electrode which is in direct contact. The invention furthermore relates to a method for producing the nonvolatile memory cell, a semiconductor arrangement having a plurality of memory cells according to the invention, and a method for producing the same.